

Figure 1. GPC of silicon oxide films deposited with different precursors at different temperatures.

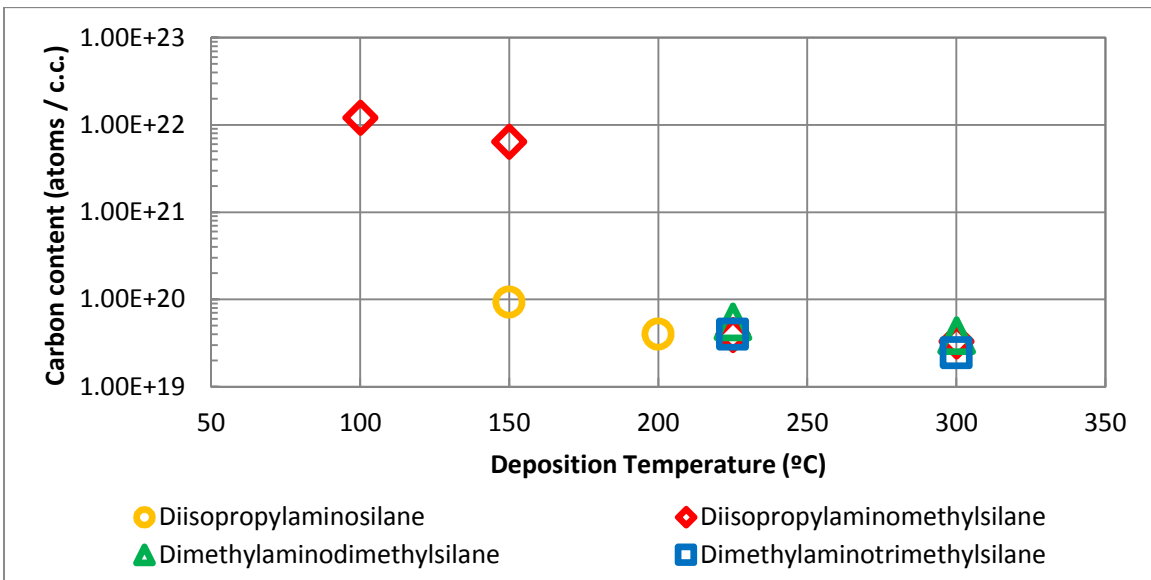


Figure 2. Carbon concentration of silicon oxide films deposited with different precursors at different temperatures, measured by SIMS.